

# SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

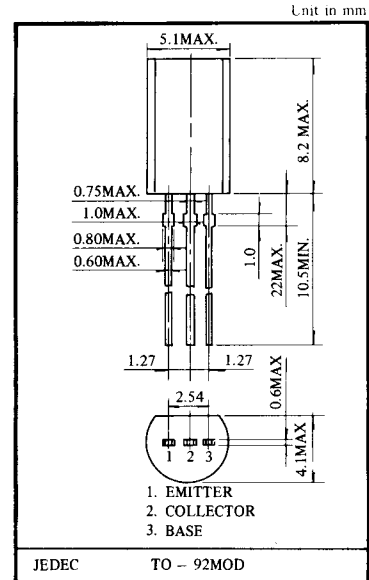
# 2SA1273

## APPLICATIONS

- Audio Power Amplifier Applications.

## FEATURES

- Complementary to 2SC 3205 and 3 Watts Output Applications.



## MAXIMUM RATINGS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-30	V	Emitter Current	$I_E$	2	A
Collector-Emitter Voltage	$V_{CEO}$	-30	V	Collector Dissipation	$P_C$	1	W
Emitter-Base Voltage	$V_{EBO}$	-5	V	Junction Temperature	$T_j$	150	°C
Collector Current	$I_C$	-2	A	Storage Temperature	$T_{stg}$	-55 ~ 150	°C

## ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -30V, I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE}$	$V_{CE} = -2V, I_C = -500mA$	100	-	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$	-	-	-2.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -2V, I_C = -500mA$	-	-	-1.0	V
Transition Frequency	$f_T$	$V_{CE} = -2V, I_C = -500mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	48	-	pF

**NOTE: According to  $h_{FE}$ , Classified as follows.**

0	100-200	Y	160-320